

outputting said part of said plurality of data to said data output node;
reading another part of said plurality of data from said memory cell; and
outputting said another part of said plurality of data to said data output node.

Actual

14. The method according to claim 13, wherein
said step of outputting said part of said plurality of data overlaps with said step of
reading another part of said plurality of data.

15. A method for reading data from a non-volatile semiconductor memory
device, said non-volatile semiconductor memory device including
a word line;
first and second bit lines;
a first memory cell coupled to said word line and said first bit line,
a second memory cell coupled to said word line and said second bit line, and
a data output node for outputting said data from said first and second memory
cells, said method comprising the steps of:
reading first data from said first memory cell with selectively activating said word
line;
outputting said first data to said data output node;
reading second data from said second memory cell with selectively activating said
word line; and
outputting said second data to said data output node, wherein